



N - CHANNEL ENHANCEMENT MODE POWER MOSFET

TF050N06MG

● General Description

The TF050N06 MG uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

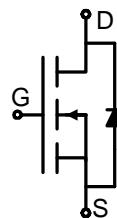
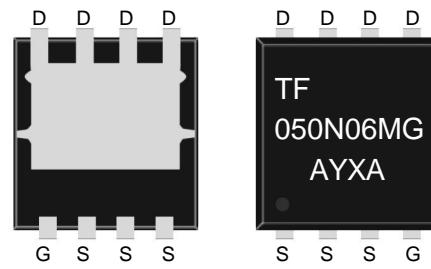
● Features

- Advance device construction
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

● Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Power Tools

● Product Summary

 $V_{DS} = 60V \quad I_D = 60A$ $R_{DS(ON)(10V\ typ)} = 5.8m\Omega$ $R_{DS(ON)(4.5V\ typ)} = 7.7m\Omega$ 

PDFNWB3.3x3.3-8L

● Package Marking and Ordering Information:

Part NO.	TF050N06MG
Marking1	050N06MG
Marking2	TF:tuofeng; AA:device code; Y:year code; X:Week
Basic ordering unit	5000 / PCS

● Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	60	A
	$I_D @ T_C = 75^\circ C$	42	A
	$I_D @ T_C = 100^\circ C$	36	A
Pulsed Drain Current ①	I_{DM}	180	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	55	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	75	mJ



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

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• Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	5.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	55	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

• Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	60	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA	1.2	1.8	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60 V _{GS} = 0V	-	-	1.0	μA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} = 0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	5.8	7.0	mΩ
		V _{GS} =4.5V, I _D =15A	-	7.7	8.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 25V, I _D =20A	-	12	-	S
Source-drain voltage	V _{SD}	I _S =20A	-	-	1.20	V

• Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =30V	-	1268	-	pF
Output capacitance	C _{oss}		-	318	-	
Reverse transfer capacitance	C _{rss}		-	13	-	

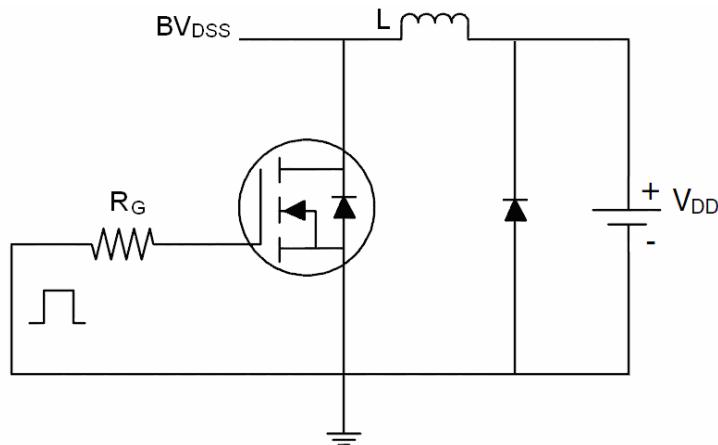
• Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 30V I _D = 10A V _{GS} = 10V	-	22.2	-	nC
Gate - Source charge	Q _{gs}		-	3.40	-	
Gate - Drain charge	Q _{gd}		-	4.64	-	

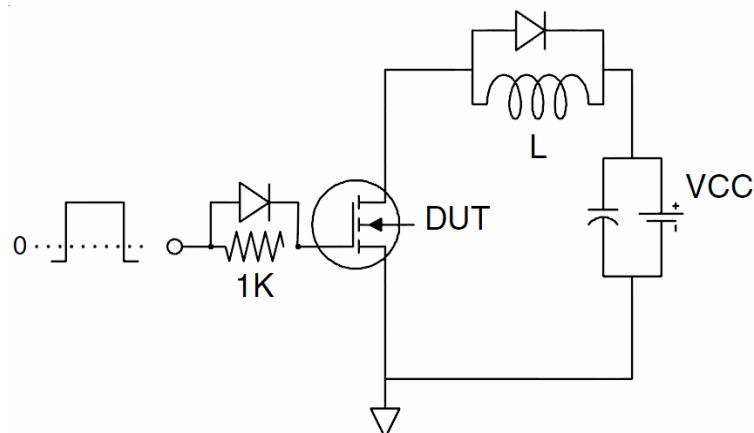
Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Test Circuit

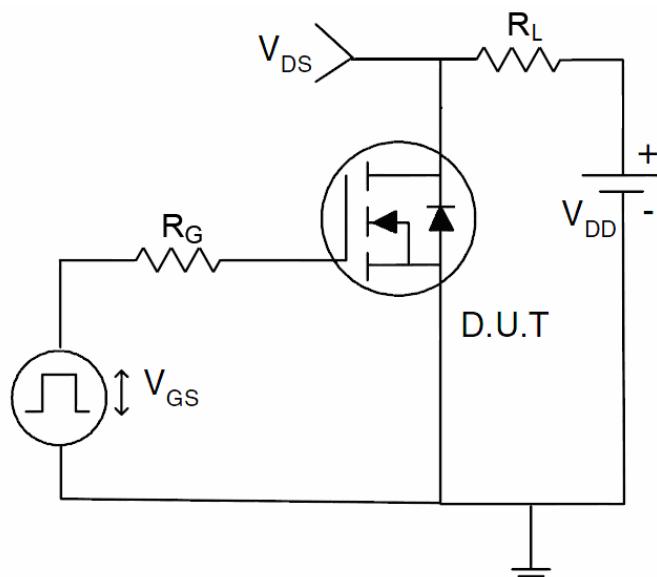
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



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Typical Electrical and Thermal Characteristics

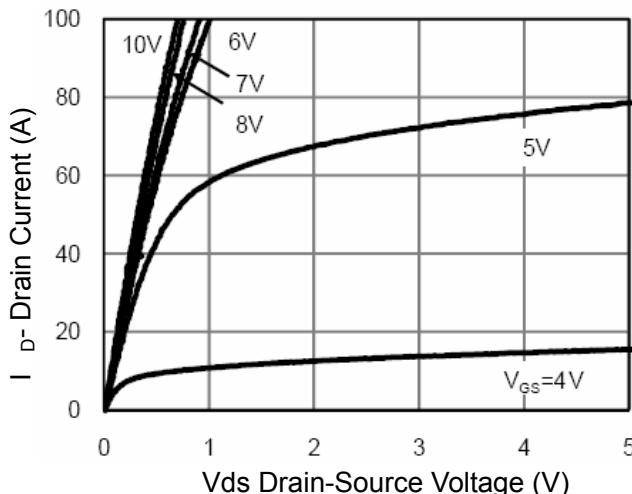


Figure 1 Output Characteristics

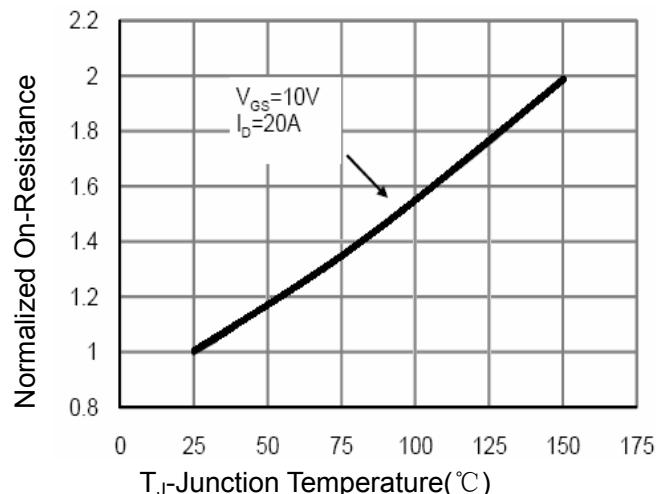


Figure 4 Rdson-JunctionTemperature

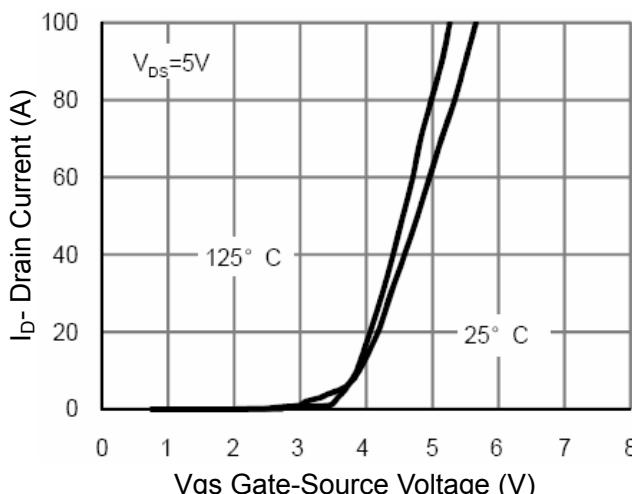


Figure 2 Transfer Characteristics

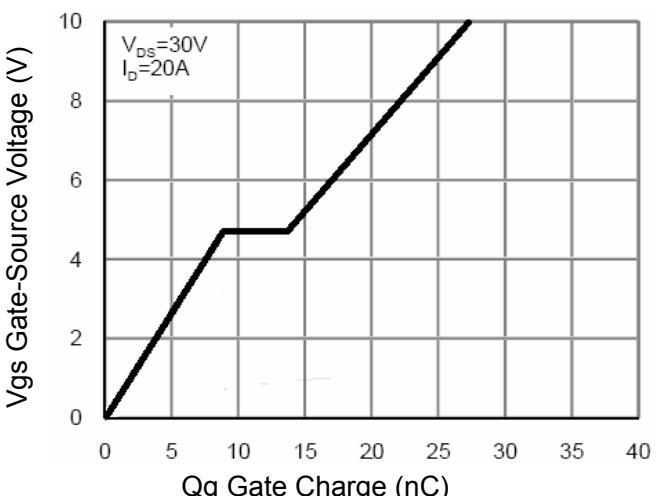


Figure 5 Gate Charge

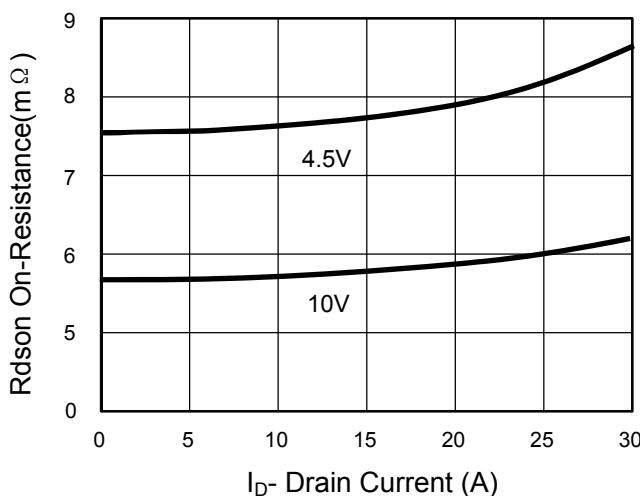


Figure 3 Rdson- Drain Current

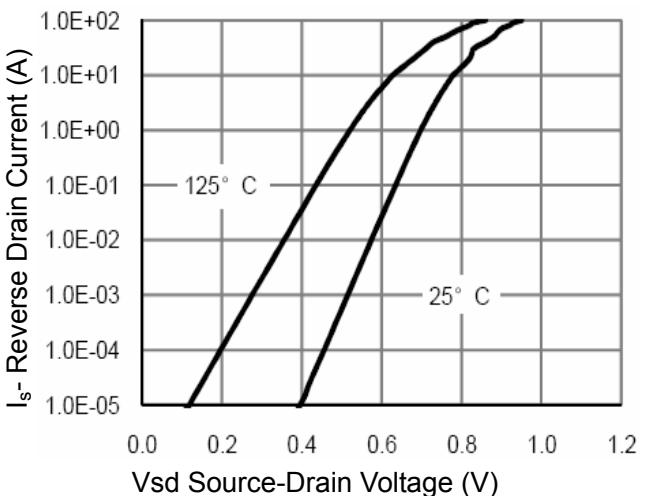


Figure 6 Source- Drain Diode Forward

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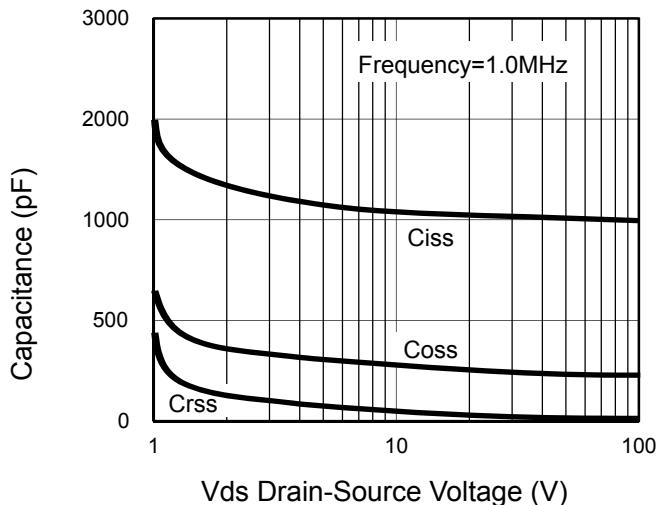


Figure 7 Capacitance vs Vds

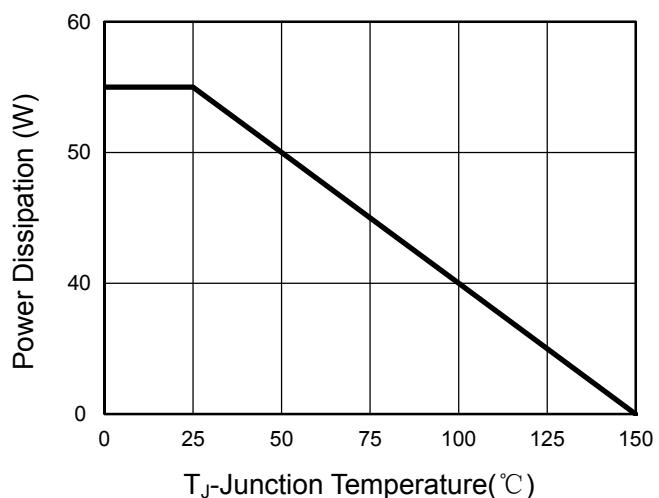


Figure 9 Power De-rating

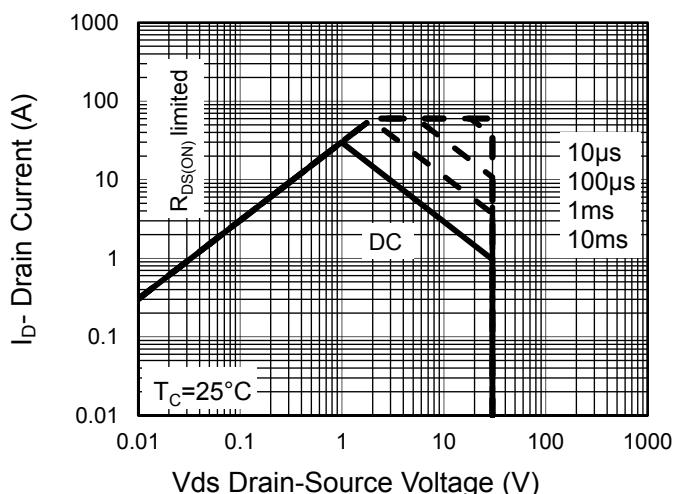


Figure 8 Safe Operation Area

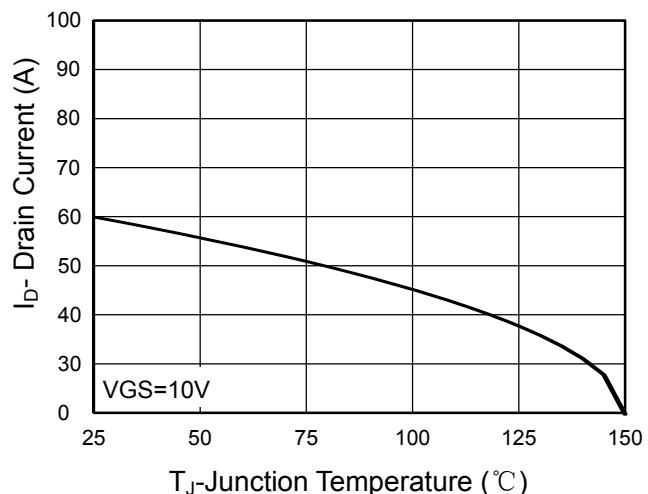


Figure 10 Current De-rating

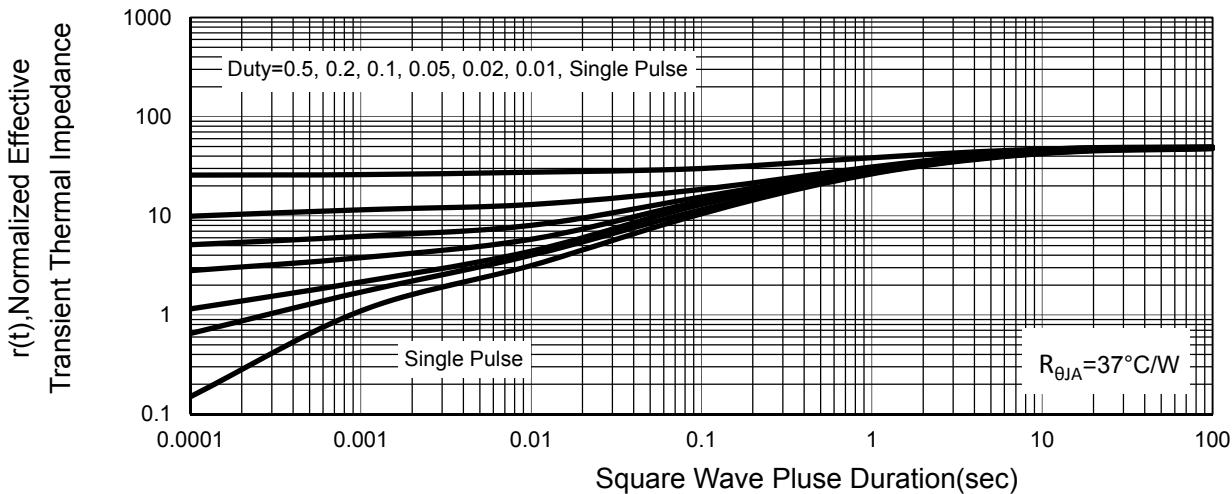
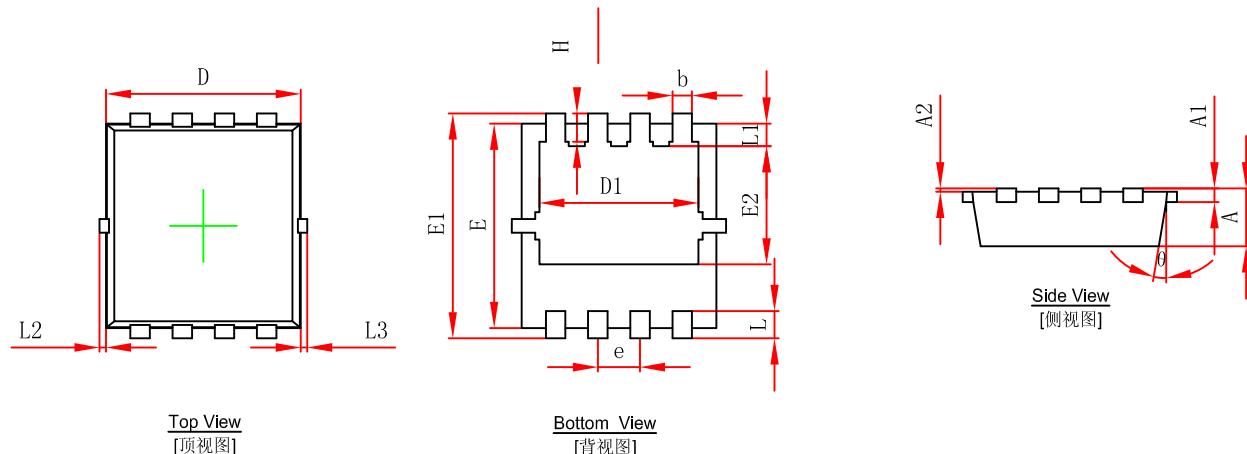


Figure 11 Normalized Maximum Transient Thermal Impedance

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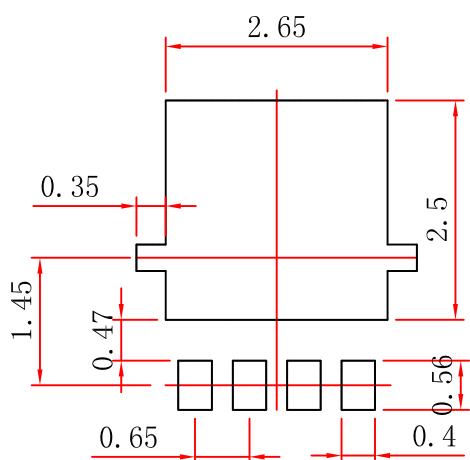
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PDFNWB3.3x3.3-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°

PDFNWB3.3x3.3-8L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.